ICMOVPE
XXII July 12-17, 2026
ICC JEJU, Jeju Island, Korea

Session Title:	**[WeA3] Advanced Growth Techniques - II**
Session Date:	**July 15 (Wed.), 2026**
Session Time:	**15:35-17:05**
Session Room:	**Room A (Baekrok Hall B-1, 1F)**
Session Chairs	

[WeA3-1] [Invited] **15:35-16:05**

Epitaxial Growth of III-Nitride Semiconductors and Their LED Structures

Zhe Zhuang, Yimeng Sang, and Bin Liu, Nanjing University, China

[WeA3-2] **16:05-16:20**

Applications of Mist Chemical Vapor Deposition in the Deposition of Inorganic Functional Thin Films

Zaichun Sun and Bingchu Mei, Wuhan University of Technology, China

[WeA3-3] **16:20-16:35**

Hybrid 3D/2D Growth Mode for High-Quality AlN on Si(111) by MOCVD

Mingtao Nong[1], Haicheng Cao[1], Tingang Liu[1], Patsy A Miranda Cortez[1], Glen Isaac Maciel García[1], Xiao Tang[2], Che-Hao Liao[3], Kexin Ren[1], Zixian Jiang[1], and Xiaohang Li[1], [1] King Abdullah University of Science and Technology, Saudi Arabia, [2] University of Bristol, United Kingdom, [3] National Yunlin University of Science and Technology, Taiwan

[WeA3-4] **16:35-16:50**

Novel MOCVD Selective Area Growth of InGaAs/GaAs/AlGaAs Using SOI Shadow Mask and Its Application to COMD Free 980nm Laser

Akihiko Kasukawa[1], I. Novitasari[1], Z-J. Sun[1], A. Albert[1], S. L. Lee[1], and M. Arai[2], [1] National Taiwan University of Science and Technology, Taiwan, [2] University of Miyazaki, Japan

[WeA3-5] **16:50-17:05**

Formation Mechanisms of Cubic GaN Grown in Si Inverted Pyramids by Selective Area OMVPE

David A. Lister, Cyan Kim, Melissa Radford, Sarah Fortin, Karen L. Kavanagh, and Simon Watkins, Simon Fraser University, Canda